

ABSTRACT OF THE DISCLOSURE

A semiconductor device (1) of the present invention includes a semiconductor element (103) including electrode parts (104), and a wiring substrate (108) including an insulation layer (101), electrode-part-connection electrodes (102) provided in the insulation layer (101), and external electrodes (107) that is provided in the insulation layer (101) and that is connected electrically with the electrode-part-connection electrodes (102), in which the electrode parts (104) and the electrode-part-connection electrodes (102) are connected electrically with each other. The insulation layer (101) has an elastic modulus measured according to JIS K6911 of not less than 0.1 GPa and not more than 5 GPa, and the electrodes (104) and the electrode-part-connection electrodes (102) are connected by metal joint.